

Title	Time resolved luminescence properties of Al _{0.3} for spin-injection into organic semiconductor
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Citation	Journal of Magnetism and Magnetic Materials, 272-276(3): 1921-1923
Issue Date	2004-05
Type	Journal Article
Text version	author
URL	http://hdl.handle.net/10119/4941
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Description	

Time resolved luminescence properties of Alq_3 for spin-injection into organic semiconductor

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Abstract

The electroluminescence and conduction properties of organic light emitting devices(OLEDs) with Alq_3 emissive layer and with Fe cathode were investigated. The relative luminescence intensity for the device became lower than that with Al cathode. Time resolved photoluminescence of Alq_3 was measured to investigate the electronic state of the interface between Fe and Alq_3 layer of OLEDs. The difference of luminescence intensities of OLEDs could not be explained only due to the work functions, but also due to the essential increase of quenching centers. © 2001 Elsevier Science. All rights reserved.

Keywords: Electroluminescence; Time resolved photoluminescence; Organic semiconductor

PACS: 78.47.+p; 78.60.Fi

Recently, spin-polarized electroluminescence(EL) due to spin-injection into inorganic light-emitting devices were observed[1]. Also, the study related with spin-injection into organic semiconductor attracts much attention[2], although spin-polarized EL using the organic molecule as an emitter has not been observed. In investigations of OLEDs, no ferromagnetic electrode has been used except for Ref. [3]. Because ferromagnetic metal(ex. Fe, Co, Ni) have relatively high work function, it causes decrease of luminescent efficiency of OLEDs[4]. In this work, EL and electronic conduction properties of OLEDs with Fe cathodes as a spin injector were investigated. Also, in order to investigate electronic states of the interface between cathode and emissive layer of OLEDs, time resolved photoluminescence(PL) properties of *tris*-(8-hydroxyquinolino)-aluminum(Alq_3) thin films deposited on Fe films were measured.

The stacking structure of our OLEDs was glass-substrate/ITO(thickness: 20 or 40 nm)/TPD(45 nm)/ Alq_3 (45, 55 or 65 nm)/Al-oxide(Al-O: 1.0 nm)/M(M = Al or Fe: 20 nm)/Al(120 nm). For the sake of comparison, the devices with non-magnetic electrode Al were also investigated. ITO(In_2O_3 + SnO_2 10 wt%) transparent anode was

deposited on glass substrates by conventional magnetron sputtering. TPD(Tri-Phenyl-Diamine) as a hole transport layer, Alq_3 as an emissive layer and Al for the making of Al-O insulator were made by conventional evaporation without breaking vacuum. Pots for TPD and Alq_3 , and an electron gun for Al were used. After Al thin film deposition, the evaporation chamber was leaked for the making of Al-O layer for five minutes. Then, the cathode M(M = Al or Fe) was evaporated using an electron gun. They were deposited as slow as possible monitoring their thickness by quartz-resonator. The current-voltage and EL properties of OLEDs were measured at room temperature.

For the time resolved PL measurements, Alq_3 films(thickness: 10 nm) were deposited on M(M = Al or Fe) films(20 nm) using evaporation without breaking vacuum. The samples with the Al-O layer between Alq_3 and M were also made. Total thickness of Al-O layer(5 nm) and M films(15 nm) was 20 nm. In the case of making Al-O layer, the evaporation system was leaked at atmosphere before Alq_3 deposition. The spectra were plotted by using a streak camera equipped with a mode-lock Ti-sapphire laser at room temperature.

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Fig.1 shows current-voltage properties of OLEDs with $M = \text{Al}$ and with $M = \text{Fe}$ in the absence of applied magnetic fields. Threshold voltage of OLEDs with $M = \text{Al}$ and that of OLEDs with $M = \text{Fe}$ were about 6.5 V and 10 V, respectively. The efficiency of electron injection from Fe cathode into Alq_3 layer through Al-oxidized layer should become low essentially because of the high work function of Fe. The inset in Fig.1 shows EL spectra of the OLEDs with $M = \text{Al}$ and with $M = \text{Fe}$. Applied current density for their measurements is 25.0 mA/cm^2 that is enough to be luminous. While the difference of the peak position between their devices was little, the relative luminescence intensity for OLEDs with $M = \text{Fe}$ was about 1/40 of those with $M = \text{Al}$. The difference of intensities could not be explained only due to the work functions. One possible reason is that the changes of the molecular conformation at the interface between Fe and Alq_3 cause more quenching sites. No effects of an applied magnetic field until 0.12 T was observed on the EL measurements.

Fig.2 shows the analyses of time resolved PL spectra near 520 nm wavelength of Alq_3 on various underlayers. The time resolved PL intensity shows a relatively fast monotonous decay. In order to consider the fast decay, the signal intensity(I) was decomposed into two components with an exponential decay of an ordinary lifetime τ_2 , of 10 ns[5] and an unusual lifetime τ_1 , for the lowest unoccupied molecular orbital(LUMO) of Alq_3 using the following equation,

$$I = a_1 \times \exp(-t/\tau_1) + a_2 \times \exp(-t/\tau_2). \quad (1)$$

The estimated τ_1 for Alq_3 on Fe was 69 ps, which is half of that for Alq_3 on SiO_2 -substrate;146 ps. Interestingly, the lifetime became longer by inserting Al-oxide(Al-O) layer between the Alq_3 and Fe layers;116 ps. It should be noticed that the proportional coefficient of the part of unusual lifetime a_1 , is larger than the part of ordinary lifetime a_2 , in the case of Alq_3 on Fe compared with the case of Alq_3 on Al. From FT-IR analysis, Alq_3 molecular structure on Fe was found to become different in comparison with Alq_3 on SiO_2 -substrate or on Al, while the change was little for the molecule on Fe/Al-O. This must come from the transformation of the chemical bonding at interface between Alq_3 and Fe, resulting in a change of electronic states of the LUMO of Alq_3 on Fe and the unusual short lifetime. Neither changes of the chemical bonding nor changes of the unusual lifetime were observed for Alq_3 on Al films. Consequently, one possible reason that the relative luminescence intensity for OLEDs with $M = \text{Fe}$ was weaker than that with $M = \text{Al}$ might be that the changes of the molecular conformation at the interface between Fe and Alq_3 leads to an increase of the number of quenching centers, then OLEDs with $M = \text{Fe}$ might need higher current density for luminescence than that with $M = \text{Al}$. Effects of lowering temperature on the PL and EL

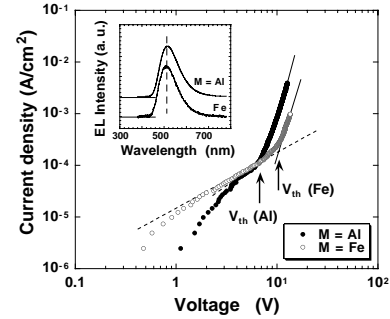


Fig. 1 Current density-voltage curves and EL spectra(inset) of OLEDs with $M = \text{Al}$ and with $M = \text{Fe}$.

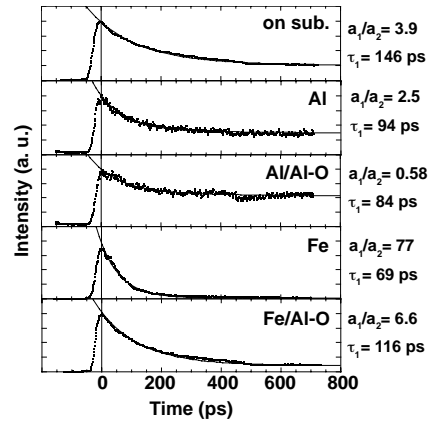


Fig.2 Time resolved PL spectra of Alq_3 thin films on various underlayers. Data were fitted by the equation (1).

properties will be investigated in the future in order to find out details of the excited states of Alq_3 .

This research is supported by JSPS Research Fellowships for Young Scientists.

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